

20V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	380mΩ@10V	0.75A
	450mΩ@4.5V	
	800mΩ@2.5V	

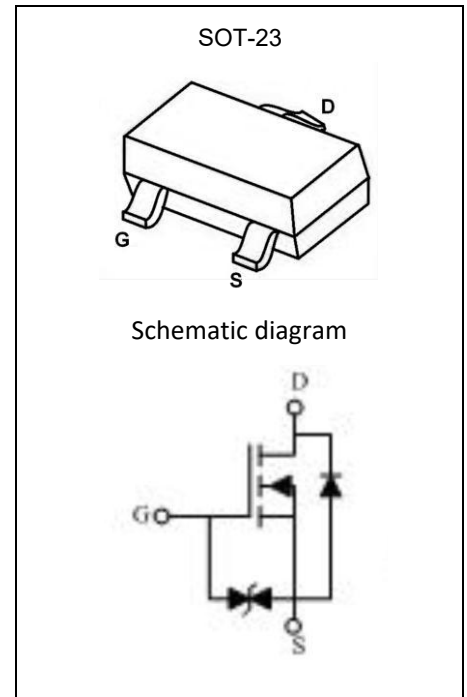
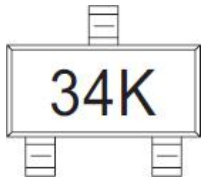
Feature

- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- VOperated at Low Logic Level Gate Drive
- ESD Protected

Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ⁽¹⁾	I_D	0.75	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	1.8	A
Power Dissipation ⁽¹⁾	P_D	0.35	W
Thermal Resistance from Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" duration for 10 s)	T_L	260	$^\circ\text{C}$

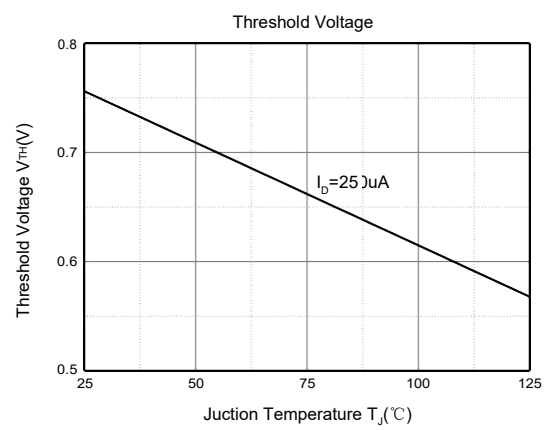
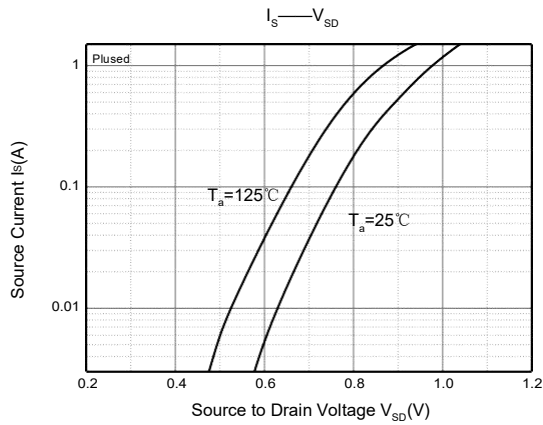
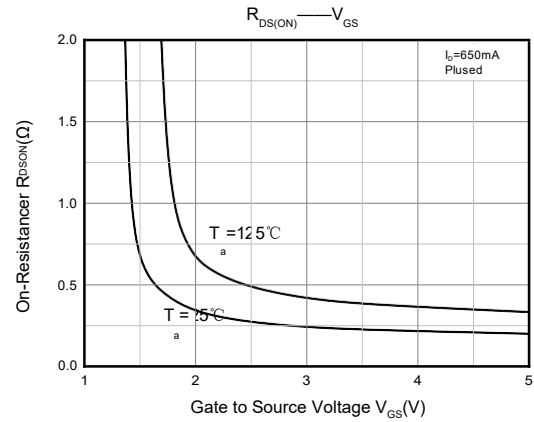
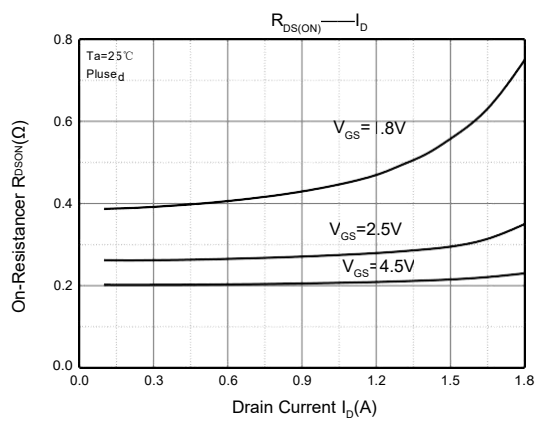
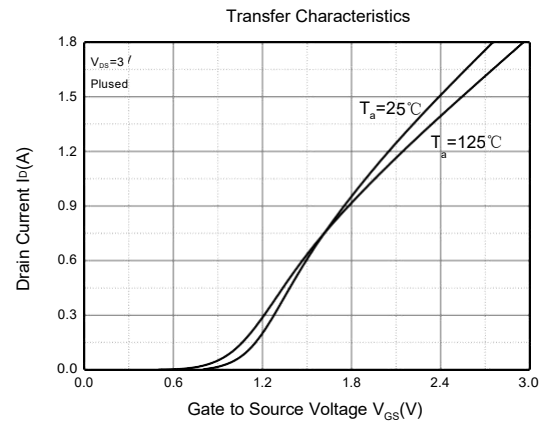
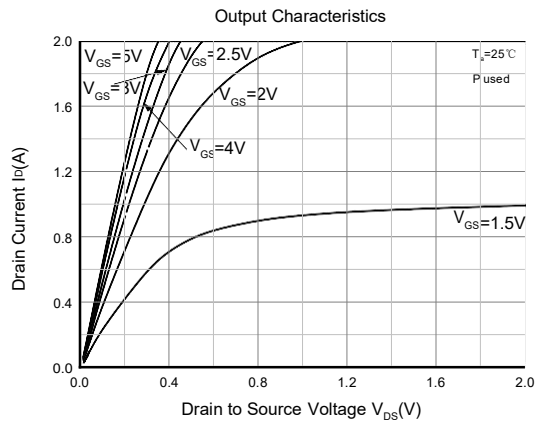
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 20	μA
Gate threshold voltage ⁽²⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.35	0.75	1.1	V
Drain-source on-resistance ⁽²⁾	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 0.65A$		190	380	m Ω
		$V_{GS} = 2.5V, I_D = 0.55A$		260	450	
		$V_{GS} = 1.8V, I_D = 0.45A$		390	800	
Forward tranconductance ⁽²⁾	g_{FS}	$V_{DS} = 10V, I_D = 0.8A$		1.6		S
Dynamic characteristics⁽⁴⁾						
Input Capacitance	C_{iss}	$V_{DS} = 16V, V_{GS} = 0V, f = 1MHz$		79	120	pF
Output Capacitance	C_{oss}			13	20	pF
Reverse Transfer Capacitance	C_{rss}			9	15	pF
Switching Characteristics⁽⁴⁾						
Turn-on delay time ⁽³⁾	$t_{d(on)}$	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_D = 500mA, R_{GEN} = 10\Omega$		6.7		ns
Turn-on rise time ⁽³⁾	t_r			4.8		ns
Turn-off delay time ⁽³⁾	$t_{d(off)}$			17.3		ns
Turn-off fall time ⁽³⁾	t_f			7.4		ns
Source-Drain Diode characteristics						
Diode Forward voltage	V_{DS}	$I_S = 0.15A, V_{GS} = 0V$			1.2	V

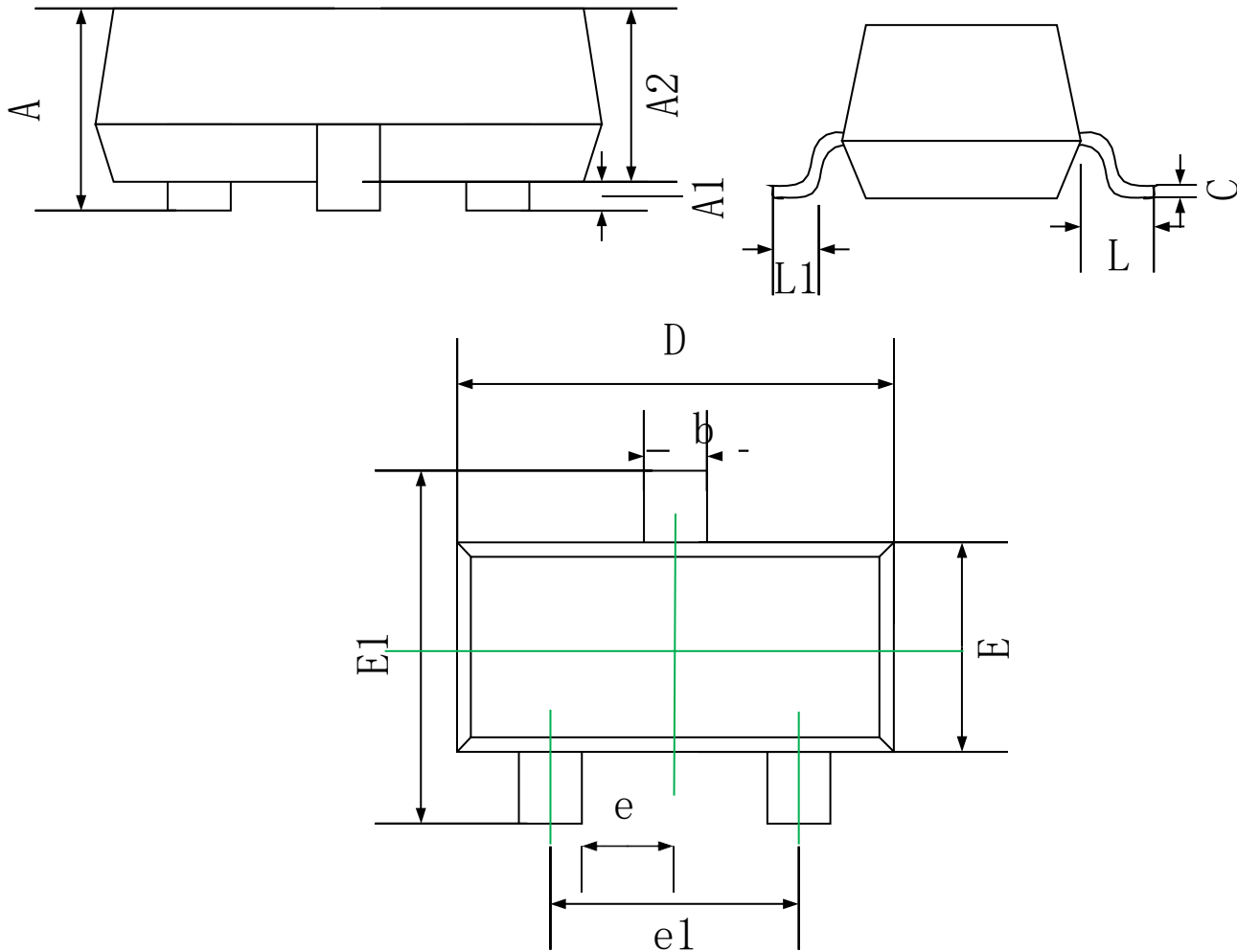
Notes:

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300 μs , Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producing.

Typical Characteristics



SOT-23 Package Information

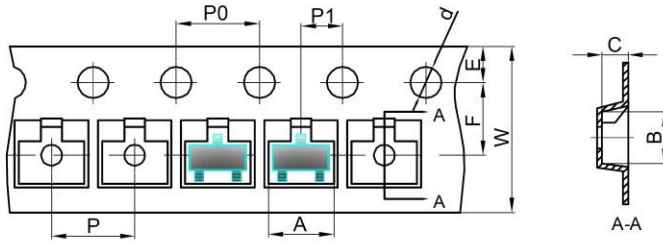


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50

SOT-23 Tape and Reel

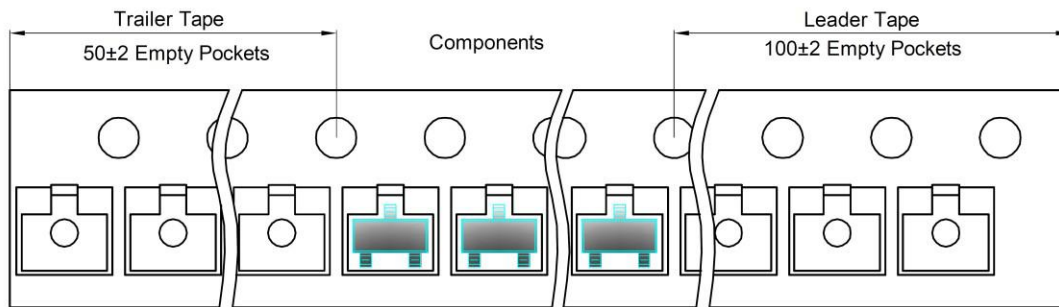
SOT-23 Tape and reel

SOT-23 Embossed Carrier Tape

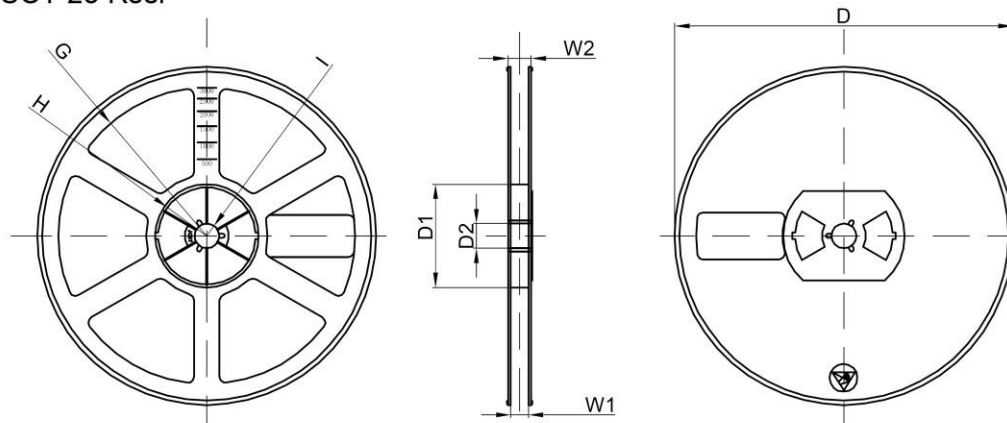


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	